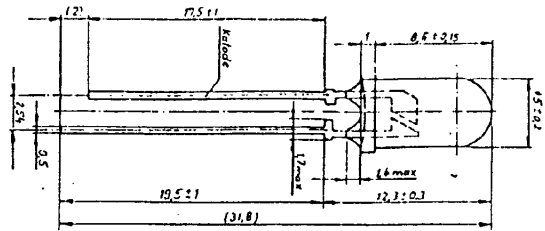


5 mm - GaAlAs - Infrared Emitter Diode



Dimensioned Scheme VX301

Limits ($T_a = 25^\circ\text{C}$)

Forward DC Current

Peak Forward Current ($t_p \leq 50 \mu\text{s}$, $\frac{t_p}{T} = 1:2$)

Surge Current ($t_p \leq 10 \mu\text{s}$)

Blocking-state Voltage

Operating Temperature Range

$I_F = 100 \text{ mA}$
 $I_{FRM} = 200 \text{ mA}$
 $I_{FRM} = 2000 \text{ mA}$
 $U_R = 5 \text{ V}$
 $T_a = -25 \dots +85^\circ\text{C}$

Ident. Terms ($T_a = 25^\circ\text{C}$, $I_F = 50 \text{ mA}$)

Parameter	Min	Typ	Max	Dimension
Forward Voltage		1,4	1,8	V
$I_F = 100 \text{ mA}$		1,5		V
Temperature Coefficient of Flow Voltage			-2,0	mV/K
Angle of Departure	θ 0,5	20		grd
Wavelength of the max. Emission		λ_p 895		nm
Spectral Band		$\Delta\lambda$ 0,5 45		nm
Radiated Power		Φ_e 15		mW
$I_F = 100 \text{ mA}$		Φ_e 30		mW
Beam Power		I_e 40		mW/sr
$I_F = 100 \text{ mA}$		I_e 80		mW/sr
Temperature Coefficient of Radiated Power		T_k 0,4		%/K
Switch Times ($I_{FRM} = 100 \text{ mA}$)		20		ns